



Product Overview

MBRD5H100T4G: Schottky Power Rectifier, Switch-mode, 5.0 A, 100 V

For complete documentation, see the data sheet

Product Description

The Schottky Rectifier employs the Schottky Barrier principle in a large metal to silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured - Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

Applications

- Power Supplies

End Products

- Power Supplies

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (uA)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
MBRD5H100T4G	Pb-free Halide free	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3
NBRD5H100T4G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3

For more information please contact your local sales support at www.onsemi.com

Created on: 7/11/2015